

# EPIGAP Optronik GmbH

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customized optoelectronics



## Product Data Sheet

### LED Chip vis

### EOLC-525-34

Rev. 01 aus 2011

Radiation	Type	Electrodes
green		P + N up

	<p>Description</p> <ul style="list-style-type: none"> <li>-Substrate: Sapphire, epitaxial layer: GaN based Material</li> <li>-N bonding pad electrode: Au alloy</li> <li>-P bonding pad electrode: Au alloy</li> </ul> <div style="text-align: center;"> <p><small>Above drawing is not on real scale.</small></p> </div>
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### Maximum Ratings

$T_{amb} = 25^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward current (DC)		$I_F$			20	mA
Peak forward current	$t_p \leq 50 \mu\text{s}$ ,	$I_{FM}$			100	mA

### Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20\text{mA}$	$V_F$		3.3	3.5	V
Reverse current	$V_R = 5\text{V}$	$I_R$			1	$\mu\text{A}$
Peak wavelength	$I_F = 20\text{mA}$	$\lambda_p$	520		522.5	nm
Full width at half maximum	$I_F = 20\text{mA}$	$\Delta\lambda$		40		nm
Luminous intensity <sup>1</sup>	$I_F = 20\text{mA}$	$I_v$	220		380	mcd

### Packing

Chips on adhesive film with wire-bond side top

We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.